MDM800E33D

FEATURES

- Low noise due to ultra soft fast recovery diode.
- High reliability, high durability diodes.
- Isolated heat sink (terminal to base).

ABSOLUTE MAXIMUM RATINGS (T_C=25°C)

Item		Symbol	Unit	MDM800E33D
Repetitive Peak Reverse Voltage		V_{RRM}	V	3,300
Forward Current	DC	I_F	A	800
	1ms	I_{FM}		1,600
Junction Temperature		$T_{vj\ op}$	°C	-40 ~ +125
Storage Temperature		T_{stg}	°C	-40 ~ +125
Isolation Test Voltage	Terminals-base	V_{ISO}	V_{RMS}	6,000(AC 1 minute)
	Terminal 1-Terminal 2	$V_{ISO\ T\text{-}T}$		6,000(AC 1 minute)
Screw Torque	Terminals (M8)	-	N·m	15 (1)
	Mounting (M6)	-		6 (2)

Notes: (1) Recommended Value 15^{+0}_{-3}N·m (2) Recommended Value 5.5±0.5N·m

ELECTRICAL CHARACTERISTICS

Item	Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Repetitive Reverse Current	I_{RRM}	mA	-	2.0	20.0	VAK=3,300V, T_{vj}=125°C
Forward Voltage Drop	V_F	V	2.0	2.5	3.0	I_F=800A, T_{vj}=125°C
Reverse Recovery Time	t_{rr}	μs	0.2	0.6	1.1	V_{CC}=1,650V, I_F=800A, Ls=120nH
Reverse Recovery Loss	$E_{rr(10\%)}$	J/P	-	0.9	1.3	R_G=4.7Ω, T_{vj}=125°C (3)

Notes: (3) Counter arm: MBN800E33D VGE= ±15V
R_G are the test condition's value to define the switching characteristics not recommended value.
Please, determine the suitable R_G value after the measurement of switching waveforms
(overshoot voltage, etc.) with appliance mounted.

PACKAGE CHARACTERISTICS

Item	Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Terminal Resistance	RCE	mΩ	-	0.4	-	Tc=25°C, per arm
Stray inductance module	L_{SCE}	nH	-	35	-	per arm
Thermal Impedance	$R_{th(j\text{-}c)}$	K/W	-	-	0.026	Junction to case (par arm)
Comparative tracking index	CTI		-	600	-	
Contact Thermal Impedance	$R_{th(c\text{-}f)}$	K/W	-	0.008	-	Case to fin (par module)

* Please contact our representatives at order.
* For improvement, specifications are subject to change without notice.
* For actual application, please confirm this spec sheet is the newest revision.

MDM800E33D

DEFINITION OF TEST CIRCUIT

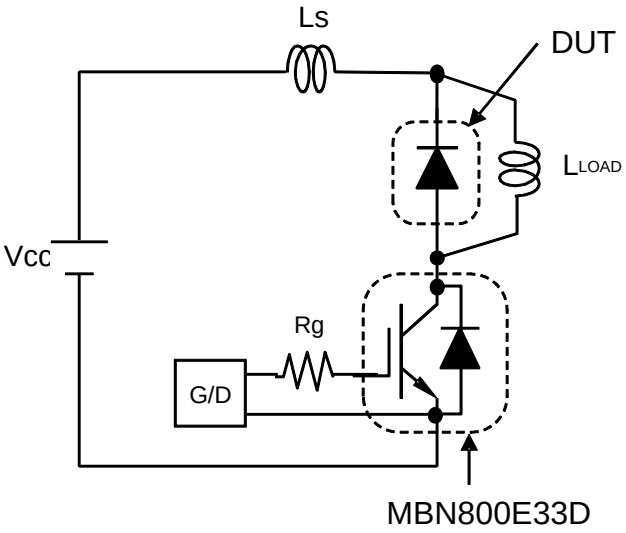
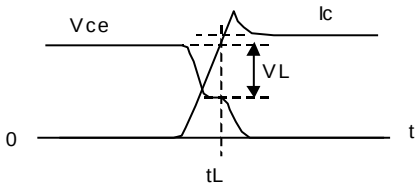
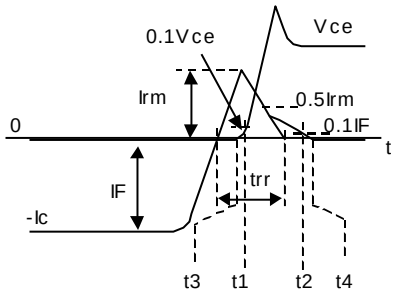


Fig.1 Switching test circuit



$$Ls = \frac{V_L}{\left(\frac{dIc}{dt}\right)_{t=t_L}}$$

Fig.2 Definition of stray inductance



$$Err(10\%) = \int_{t1}^{t2} IF \cdot Vce \, dt$$

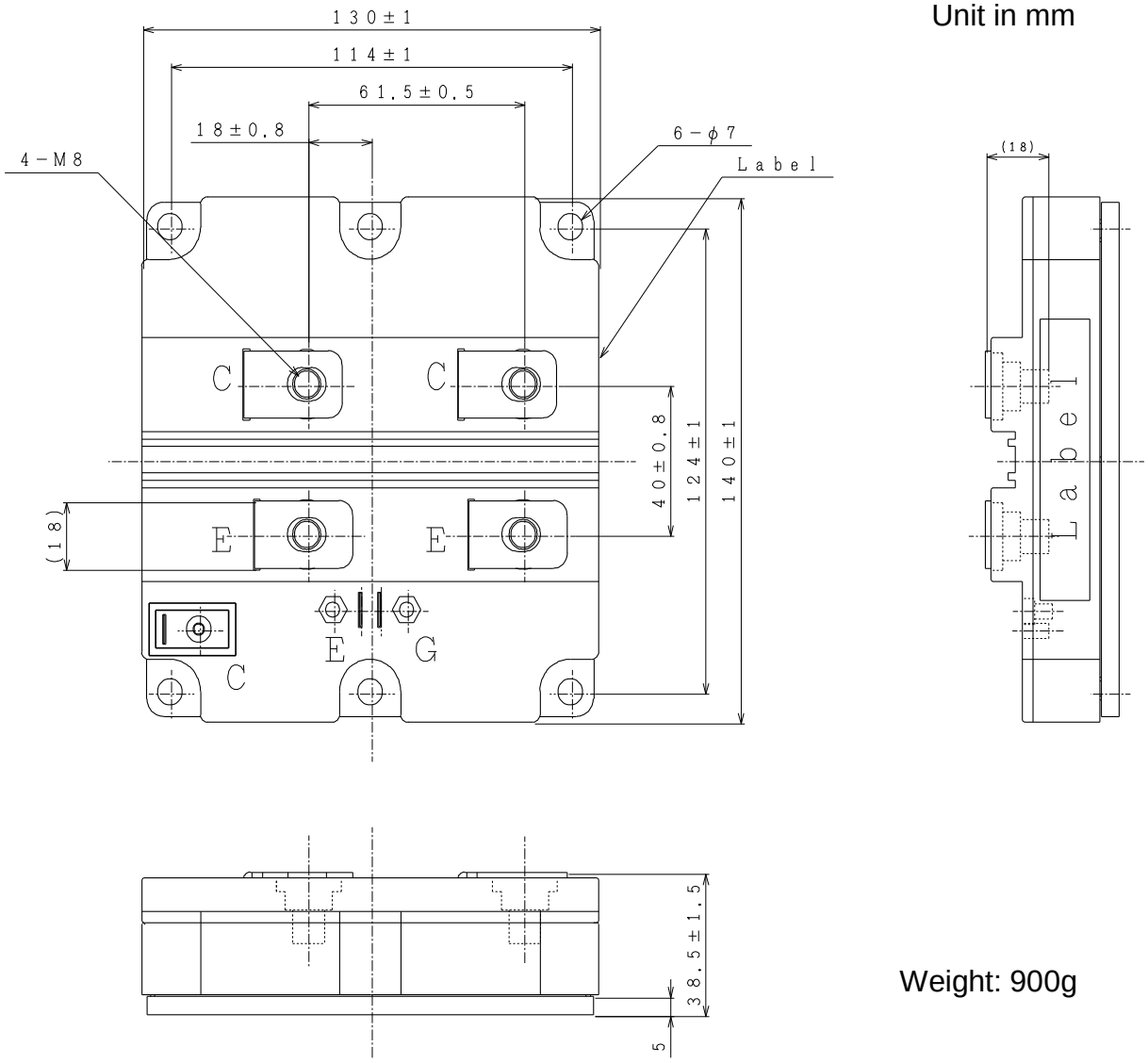
$$Err(Full) = \int_{t3}^{t4} IF \cdot Vce \, dt$$

Fig.3 Definition of switching loss

MDM800E33D

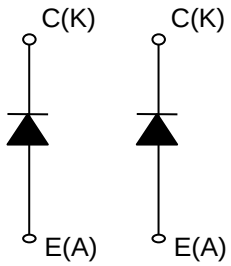
OUTLINE DRAWING

Unit in mm

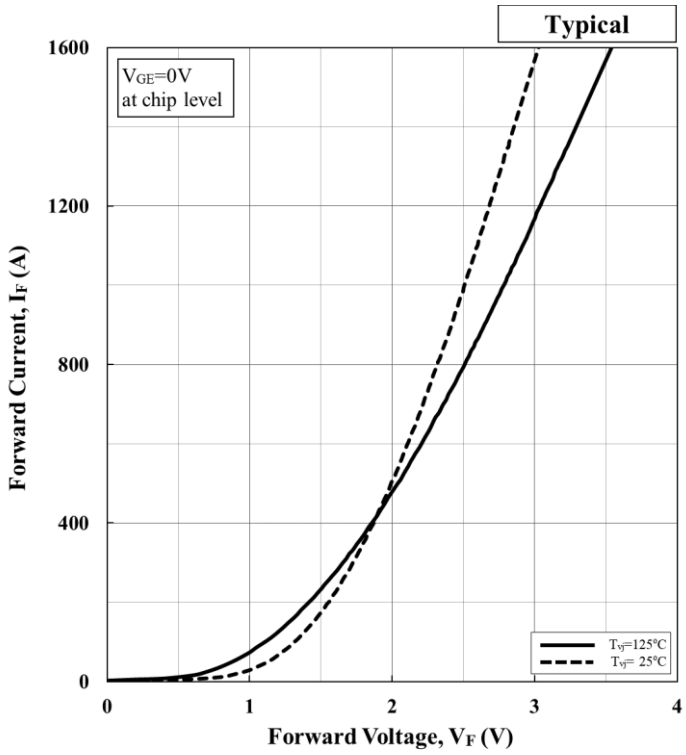


Weight: 900g

CIRCUIT DIAGRAM

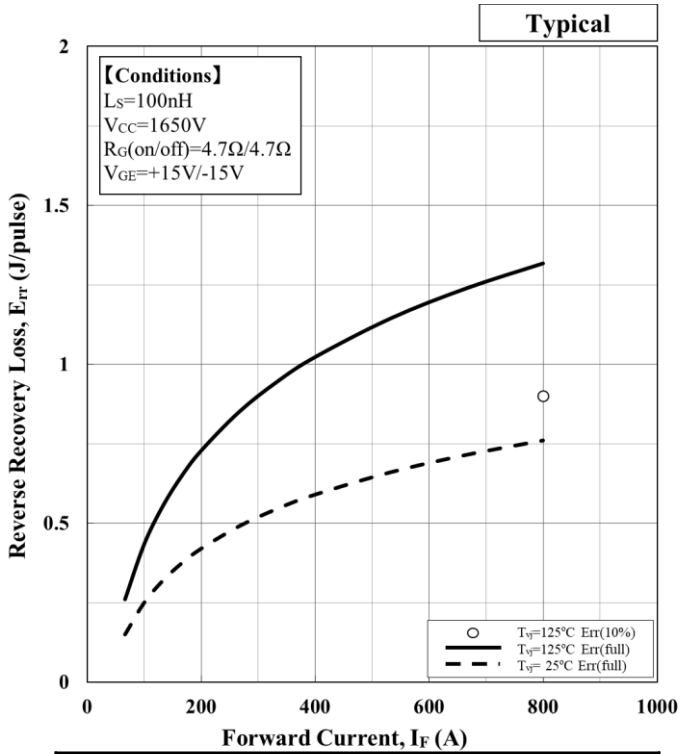


MDM800E33D



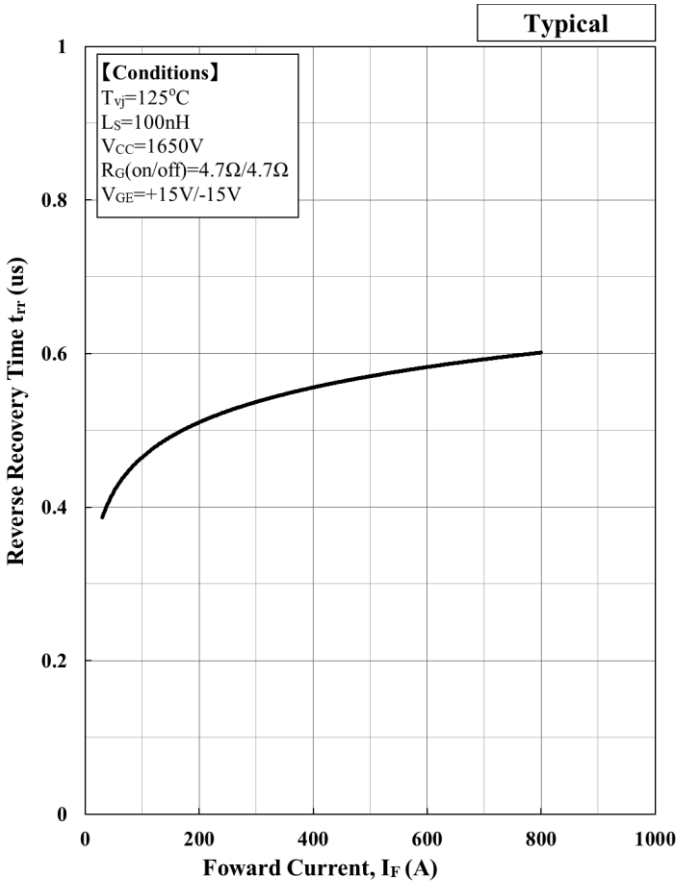
$V_F[V] = a_3 \cdot \lvert I_F \rvert^3 + a_2 \cdot \lvert I_F \rvert^2 + a_1 \cdot \lvert I_F \rvert + a_0$				
Temp.[°C]	a_3	a_2	a_1	a_0
25	3.51E-10	-1.22E-06	2.24E-03	1.13E+00
125	4.05E-10	-1.45E-06	2.97E-03	8.64E-01

Forward Voltage of diode



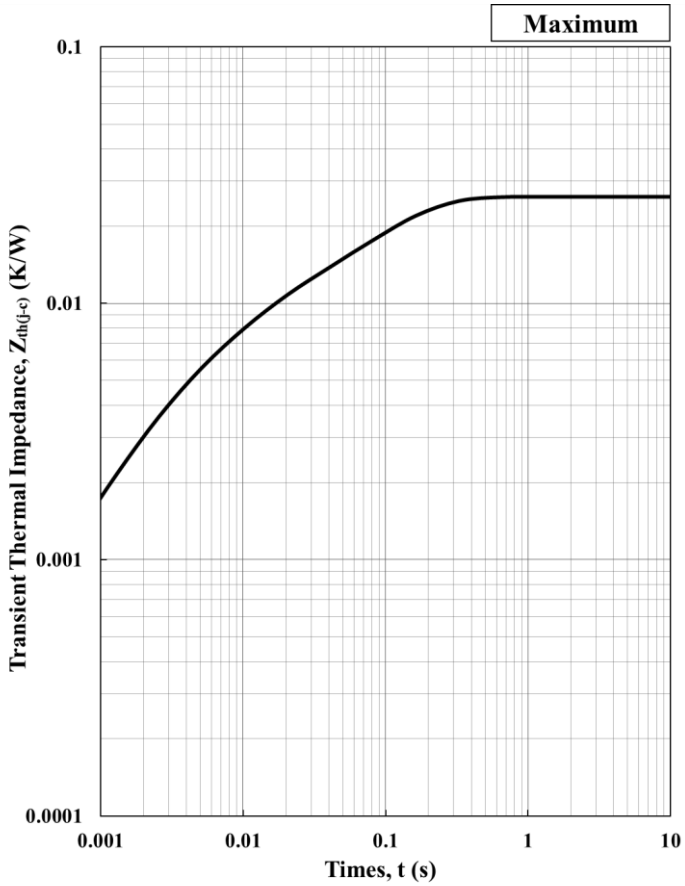
$E\ [J] = a_3 \cdot \lvert I_F \rvert^3 + a_2 \cdot \lvert I_F \rvert^2 + a_1 \cdot \lvert I_F \rvert + a_0$				
Temp.[°C]	a_3	a_2	a_1	a_0
25	2.42E-09	-4.26E-06	2.81E-03	7.70E-04
125	4.20E-09	-7.39E-06	4.89E-03	1.34E-03

Recovery loss vs. Forward current



Reverse Recovery Time vs. Foward Current

MDM800E33D



Transient Thermal Ipedance Curve

Foster model lumped circuit constant

n	1	2	3	4
R th, Diode [n]	1.73E-02	2.62E-03	6.69E-05	6.00E-03
C th, Diode [n]	6.47E+00	8.38E-01	2.36E+00	1.67E+00

Cauer model lumped circuit constant

n	1	2	3	4
R th, Diode [n]	1.71E-03	4.84E-03	6.18E-03	1.33E-02
C th, Diode [n]	4.22E-01	1.52E-01	1.46E+00	6.14E+00

Material declaration

Please note the following materials are contained in the product, in order to keep characteristic and reliability level.

Material	Contained part
Lead (Pb) and its compounds	Solder

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HITACHI POWER SEMICONDUCTORS

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